

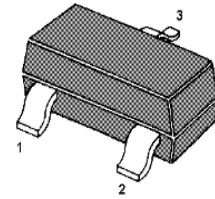
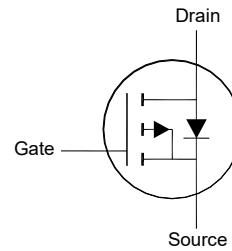
P-Channel Enhancement Mode MOSFET

Features

- AEC-Q101 Qualified
- Surface-mounted package
- Halogen and Antimony Free(HAF), RoHS compliant

Application

- Portable appliances
- Battery management



1. Gate 2. Source 3. Drain
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	$-I_D$	3.8	A
Peak Drain Current, Pulsed ¹⁾	$-I_{DM}$	11	A
Power Dissipation ²⁾	P_D	1.08	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance - Junction to Ambient ²⁾	$R_{\theta JA}$	115	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})} = 150^\circ\text{C}$

²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air, $t \leq 5 \text{ s}$.

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $-I_D = 250\ \mu\text{A}$	$-V_{(BR)DSS}$	30	-	-	V
Zero Gate Voltage Drain Current at $-V_{DS} = 30\ \text{V}$	$-I_{DSS}$	-	-	800	nA
Gate-Source Leakage at $V_{GS} = \pm 20\ \text{V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $-I_D = 250\ \mu\text{A}$	$-V_{GS(th)}$	1	-	2.1	V
Drain-Source On-State Resistance at $-V_{GS} = 10\ \text{V}$, $-I_D = 3.8\ \text{A}$ at $-V_{GS} = 4.5\ \text{V}$, $-I_D = 3\ \text{A}$	$R_{DS(ON)}$	- -	- -	70 120	m Ω
DYNAMIC PARAMETERS					
Gate Resistance at $V_{DS} = 0\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	R_g	-	5.8	-	Ω
Forward Transconductance at $-V_{DS} = 10\ \text{V}$, $-I_D = 2\ \text{A}$	g_{fs}	-	3	-	S
Input Capacitance at $-V_{DS} = 20\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_{iss}	-	410	-	pF
Output Capacitance at $-V_{DS} = 20\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_{oss}	-	47	-	pF
Reverse Transfer Capacitance at $-V_{DS} = 20\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_{rss}	-	40	-	pF
Total Gate Charge at $-V_{DS} = 20\ \text{V}$, $-I_D = 3\ \text{A}$, $-V_{GS} = 10\ \text{V}$ at $-V_{DS} = 20\ \text{V}$, $-I_D = 3\ \text{A}$, $-V_{GS} = 4.5\ \text{V}$	Q_g	- -	8.3 4	- -	nC
Gate-Source Charge at $-V_{DS} = 20\ \text{V}$, $-I_D = 3\ \text{A}$, $-V_{GS} = 10\ \text{V}$	Q_{gs}	-	1.8	-	nC
Gate-Drain Charge at $-V_{DS} = 20\ \text{V}$, $-I_D = 3\ \text{A}$, $-V_{GS} = 10\ \text{V}$	Q_{gd}	-	1.5	-	nC
Turn-On Delay Time at $-V_{DD} = 20\ \text{V}$, $-V_{GS} = 10\ \text{V}$, $-I_D = 3\ \text{A}$, $R_G = 3.3\ \Omega$	$t_{d(on)}$	-	7.6	-	nS
Turn-On Rise Time at $-V_{DD} = 20\ \text{V}$, $-V_{GS} = 10\ \text{V}$, $-I_D = 3\ \text{A}$, $R_G = 3.3\ \Omega$	t_r	-	13	-	nS
Turn-Off Delay Time at $-V_{DD} = 20\ \text{V}$, $-V_{GS} = 10\ \text{V}$, $-I_D = 3\ \text{A}$, $R_G = 3.3\ \Omega$	$t_{d(off)}$	-	9.6	-	nS
Turn-Off Fall Time at $-V_{DD} = 20\ \text{V}$, $-V_{GS} = 10\ \text{V}$, $-I_D = 3\ \text{A}$, $R_G = 3.3\ \Omega$	t_f	-	2.8	-	nS
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $-I_S = 2.7\ \text{A}$, $-V_{GS} = 0\ \text{V}$	$-V_{SD}$	-	-	1.26	V
Body-Diode Continuous Current	$-I_S$	-	-	3.8	A
Body Diode Reverse Recovery Time at $-I_S = 3\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$	t_{rr}	-	9	-	ns
Body Diode Reverse Recovery Charge at $-I_S = 3\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$	Q_{rr}	-	5	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

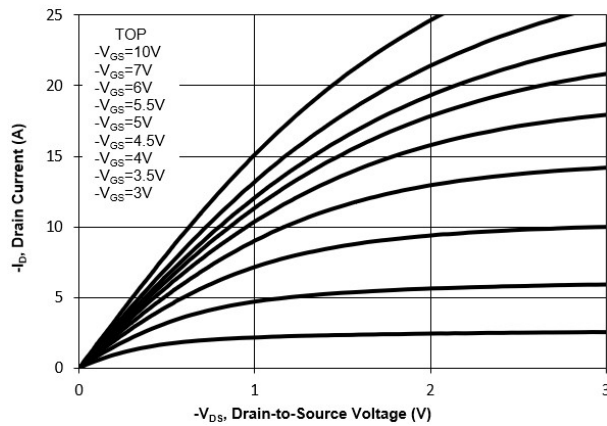


Fig. 2 Typical Transfer Characteristics

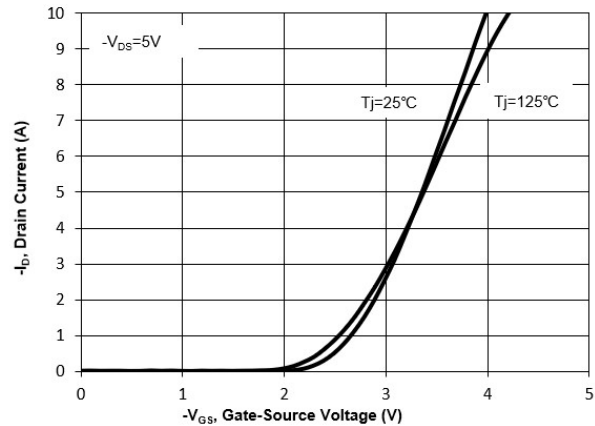


Fig. 3 on-Resistance vs Drain Current

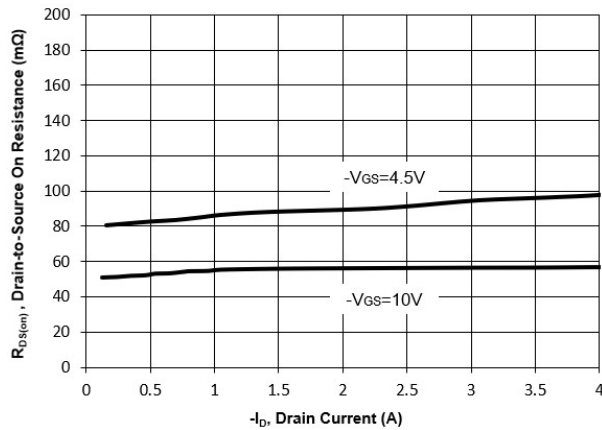


Fig. 4 on-Resistance vs. Gate Voltage

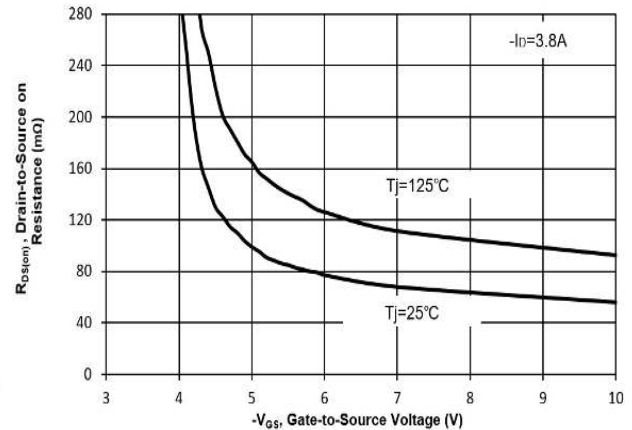
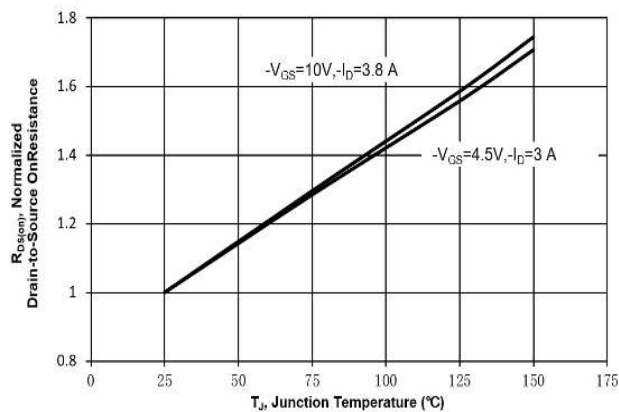
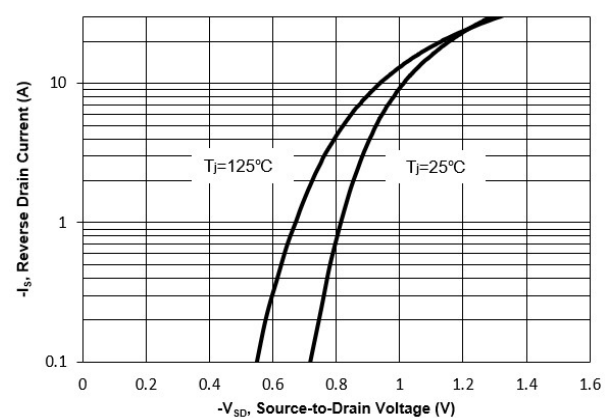
Fig. 5 on-Resistance vs. T_J 

Fig. 6 Typical Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

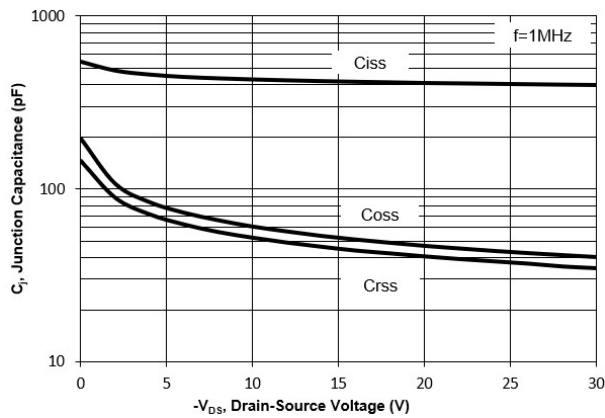
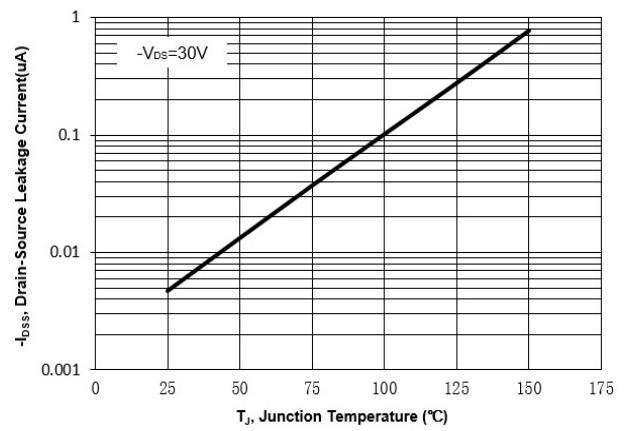
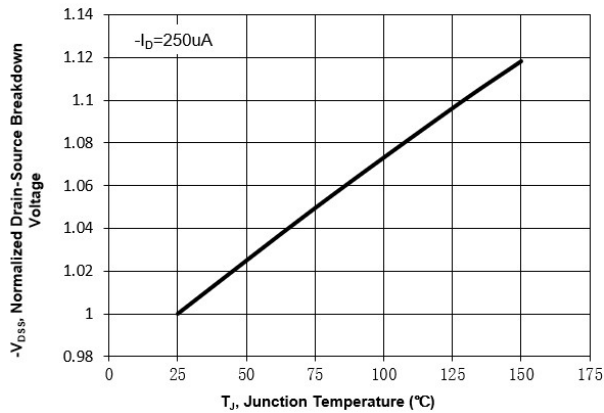
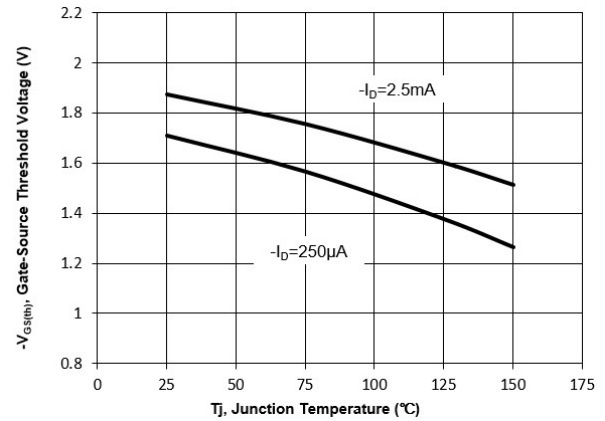
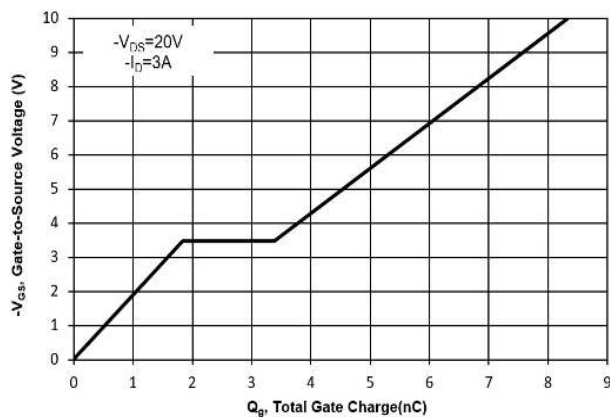
Fig. 8 Drain-Source Leakage Current vs. T_J Fig. 9 $V_{(BR)DSS}$ vs. Junction TemperatureFig. 10 Gate Threshold Variation vs. T_J 

Fig. 11 Gate Charge



Test Circuits

Fig.1-1 Switching times test circuit

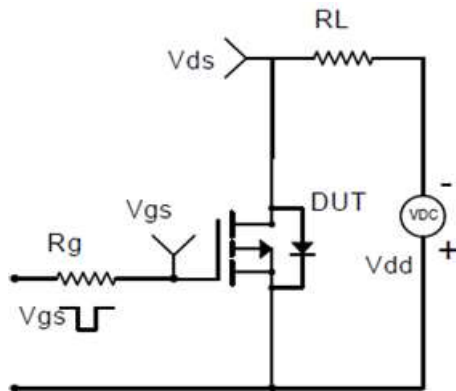


Fig.1-2 Switching Waveform

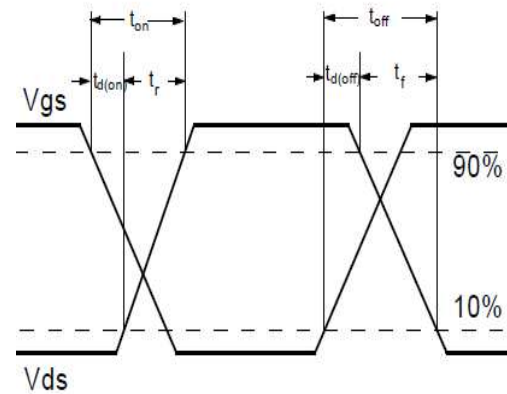


Fig.2-1 Gate charge test circuit

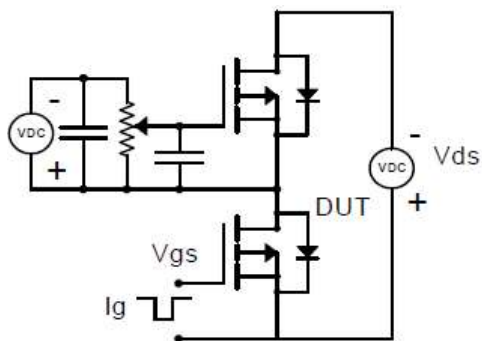
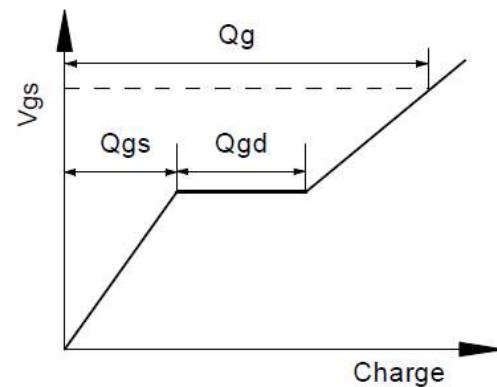
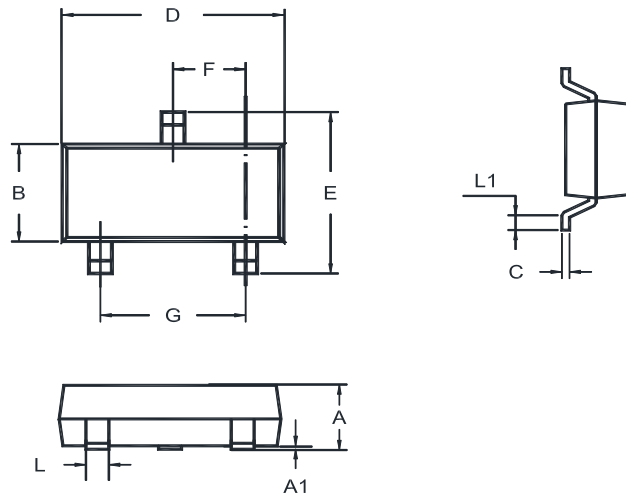


Fig.2-2 Gate charge waveform



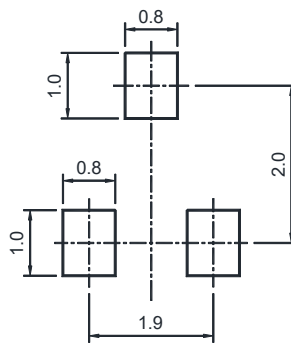
Package Outline (Dimensions in mm)

SOT-23



Unit	A	A1	B	C	D	E	F	G	L	L1
mm	1.20 0.89	0.100 0.013	1.40 1.20	0.19 0.08	3.04 2.80	2.6 2.2	1.02 0.89	2.04 1.78	0.51 0.37	0.2 MIN

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-23	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

" PG " = Part No.

" • " = HAF (Halogen and Antimony Free)

" YM " = Date Code Marking

" Y " = Year

" M " = Month

Font type: Arial

